NSN 5962-00-517-0270

Memory Microcircuit - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5962-00-517-0270

Body Length:

Between 0.750 inches and 0.795 inches

Body Width:

Between 0.245 inches and 0.300 inches

Body Height:

Between 0.150 inches and 0.180 inches

Maximum Power Dissipation Rating:

525.0 milliwatts

Operating Tempurature Range:

-55.0/+125.0 degrees celsius

Storage Tempurature Range:

-65.0/+150.0 degrees celsius

Features Provided:

Hermetically sealed and monolithic and positive outputs and programmable and programmed and w/enable and bipolar and w/open collector

Inclosure Material:

Ceramic and glass

Inclosure Configuration:

Dual-in-line

Output Logic Form:

Transistor-transistor logic

Input Circuit Pattern:

6 input

Case Outline Source And Designator:

Mo-001-ag joint electron device engineering council

Terminal Surface Treatment:

Solder

Voltage Rating And Type Per Characteristic:

5.5 volts power source

Time Rating Per Chacteristic:

70.00 nanoseconds propagation delay time, low to high level output

Memory Device Type:

Rom

Test Data Document:

07187-4005908 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.; excludes any specification, standard or other document that may be referenced in a basic governing drawing)

Terminal Type And Quantity:

16 printed circuit

Shelf Life:

N/a

Unit Of Measure:

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Demilitarization:

Yes - demil/mli

NSN 5962-00-517-0270

Memory Microcircuit - Page 2 of 2

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